

60V N-CHANNEL SELF PROTECTED ENHANCEMENT MODE IntelliFET MOSFET

Product Summary

Continuous Drain Source Voltage: 60V

On-State Resistance: 500mΩ

Nominal Load Current (V_{IN} = 5V): 1.3A

Clamping Energy: 90mJ

Description

The DIODES™ ZXMS6004FF is a self-protected low side IntelliFET® MOSFET with logic level input. It integrates overtemperature, overcurrent, overvoltage (active clamp) and ESD protected logic level functionality. The ZXMS6004FF is ideal as a general purpose switch driven from 3.3V or 5V microcontrollers in harsh environments where standard MOSFETs are not rugged enough.

Applications

- Especially suited for loads with a high in-rush current such as lamps and motors
- All types of resistive, inductive and capacitive loads in switching applications
- μC compatible power switches for 12V and 24V DC applications
- Automotive rated
- Replaces electromechanical relays and discrete circuits
- Linear mode capabilities the current-limiting protection circuitry
 is designed to de-activate at low V_{DS} to minimize on state power
 dissipation. The maximum DC operating current is therefore
 determined by the thermal capability of the package/board
 combination, rather than by the protection circuitry. This does not
 compromise the product's ability to self-protect at low V_{DS}.

Features and Benefits

- Compact High Power Dissipation Package
- Low Input Current
- Logic Level Input (3.3V and 5V)
- Short Circuit Protection with Auto Restart
- Over Voltage Protection (Active Clamp)
- Thermal Shutdown with Auto Restart
- Overcurrent Protection
- Input Protection (ESD)
- High Continuous Current Rating
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

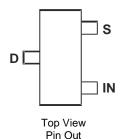
https://www.diodes.com/products/automotive/automotive-products/.

- This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.
 - https://www.diodes.com/quality/product-definitions/
- An Automotive-Compliant Part is Available Under Separate Datasheet (ZXMS6004FFQ)

Mechanical Data

- Package: SOT23F
- Package Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.012 grams (Approximate)





Ordering Information (Note 4)

Part Number	Package Marking		Reel Size (inches)	Tape Width (mm)	Packing	
	Package	Warking	Reel Size (Iliches)	rape widin (iliin)	Qty.	Carrier
ZXMS6004FFTA	SOT23F	1K6	7	12	3,000	Reel

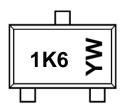
Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

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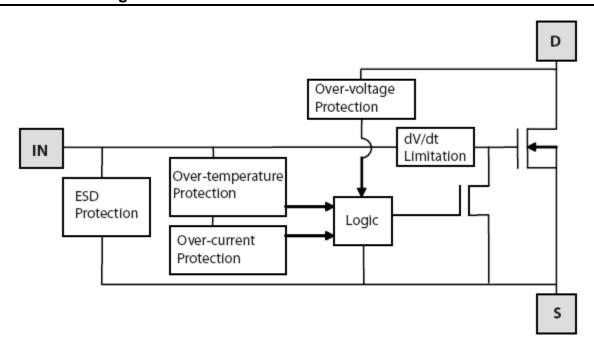


Marking Information



1K6 = Product Type Marking Code Y or \overline{Y} : Year: 0 to 9 (ex: 2 = 2022) W or \overline{W} : Week: A to Z: Week 1 to 26 a to z: Week 27 to 52 z: Represents Week 52 & 53

Functional Block Diagram





Absolute Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Continuous Drain-Source Voltage	V _{DS}	60	V
Drain-Source Voltage for Short Circuit Protection	V _{DS} (SC)	36	V
Continuous Input Voltage	Vin	-0.5 +6	V
Continuous Input Current @-0.2V \leq V _{IN} \leq 6V Continuous Input Current @V _{IN} $<$ -0.2V or V _{IN} $>$ 6V	lin	No Limit I _{IN} ≤ 2	mA
Pulsed Drain Current @V _{IN} = 3.3V	I _{DM}	2	Α
Pulsed Drain Current @V _{IN} = 5V	I _{DM}	2.5	Α
Continuous Source Current (Body Diode)	Is	1	Α
Pulsed Source Current (Body Diode)	Ism	5	Α
Unclamped Single Pulse Inductive Energy T _J = +25°C, I _D = 0.5A, V _{DD} = 24V	Eas	90	mJ
Electrostatic Discharge (Human Body Model)	Vesd	4,000	V
Charged Device Model	V _{CDM}	1,000	V

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation @T _A = +25°C (Note 5) Linear Derating Factor	P _D	0.83 6.66	W mW/°C
Power Dissipation @T _A = +25°C (Note 6) Linear Derating Factor	PD	1.5 12.0	W mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	Reja	150	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	Reja	83	°C/W
Thermal Resistance, Junction to Case (Note 7)	Rejc	44	°C/W
Operating Temperature Range	TJ	-40 to +150	°C
Storage Temperature Range	T _{STG}	-55 to +150	°C

Recommended Operating Conditions

The ZXMS6004FF is optimized for use with μC operating from 3.3V and 5V supplies.

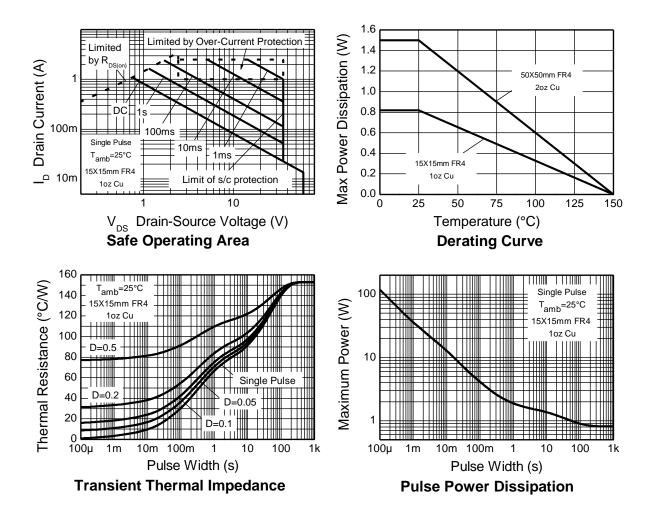
Characteristic	Symbol	Min	Max	Unit
Input Voltage Range	Vin	0	5.5	V
Ambient Temperature Range	TA	-40	+125	°C
High Level Input Voltage for MOSFET to be On	V _{IH}	3	5.5	V
Low Level Input Voltage for MOSFET to be Off	VIL	0	0.7	V
Peripheral Supply Voltage (Voltage to Which Load is Referred)	VP	0	36	V

Notes:

- 5. For a device surface mounted on 15mm x 15mm single sided, 1oz weight copper on 1.6mm FR4 board, in still air conditions.
 6. For a device surface mounted on 50mm x 50mm single sided, 2oz weight copper on 1.6mm FR4 board, in still air conditions.
 7. Thermal resistance from junction and the mounting surfaces of the drain pins.



Typical Thermal Characteristics





Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Static Characteristics						
Drain-Source Clamp Voltage	VDS(AZ)	60	65	70	V	I _D = 10mA
Off-State Drain Current		_	_	500	nA	V _{DS} = 12V, V _{IN} = 0V
Oli-State Dialii Cullent	IDSS	-	_	1	μA	V _{DS} = 36V, V _{IN} = 0V
Input Threshold Voltage	VIN(TH)	0.7	1	1.5	V	V _{DS} = V _{GS} , I _D = 1mA
Input Current	lu.	_	60	100	μΑ	$V_{IN} = +3V$
Input Current	lin	-	120	200		V _{IN} = +5V
Input Current while Overtemperature Active	_	1	_	220	μA	$V_{IN} = +5V$
Static Drain-Source On-State Resistance	Descer	_	400	600	mΩ	$V_{IN} = +3V$, $I_D = 0.5A$
Static Diani-Source Oil-State Resistance	RDS(ON)	-	350	500	11122	$V_{IN} = +5V, I_D = 0.5A$
Continuous Drain Current (Note 5)		0.9	_	_		V _{IN} = 3V, T _A = +25°C
Continuous Diain Current (Note 5)		1.0	_	_	А	V _{IN} = 5V, T _A = +25°C
Continuous Drain Current (Note 6)	ID	1.2	_	_		V _{IN} = 3V, T _A = +25°C
Continuous Diain Current (Note 6)		1.3	_	_		V _{IN} = 5V, T _A = +25°C
Current Limit (Note 8)	I _{D(LIM)}	0.7	1.7	_	А	$V_{IN} = +3V$
Current Limit (Note 8)		1	2.2	_	А	$V_{IN} = +5V$
Dynamic Characteristics						
Turn-On Delay Time	t _{D(ON)}	_	5	_		V _{DD} = 12V, I _D = 0.5A, V _{GS} = 5V
Rise Time	t _R	_	10	_		
Turn-Off Delay Time	tD(OFF)	_	45	_	μs	
Fall Time	tF	_	15	_		
Overtemperature Protection						
Thermal Overload Trip Temperature (Note 9)	T _{JT}	+150	+175	_	°C	
Thermal Hysteresis (Note 9)	fF		+10		°C	

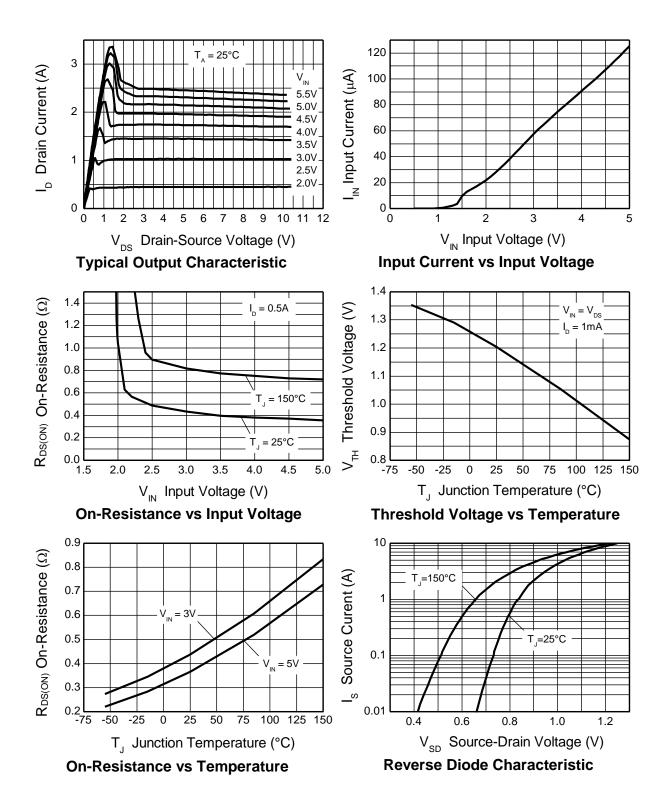
Notes:

- 5. For a device surface mounted on 15mm x 15mm single sided, 1oz weight copper on 1.6mm FR4 board, in still air conditions. 6. For a device surface mounted on 50mm x 50mm single sided, 2oz weight copper on 1.6mm FR4 board, in still air conditions.
- 7. Thermal resistance from junction and the mounting surfaces of the drain pins.
- 8. The drain current is restricted only when the device is in saturation (see graph 'Typical Output Characteristic'). This allows the device to be used in the fully on-state without interference from the current limit. The device is fully protected at all drain currents, as the low power dissipation generated outside
- saturation makes current limit unnecessary.

 9. Overtemperature protection is designed to prevent device from destruction under fault conditions. Fault conditions are considered as "outside" normal operating range, so this part is not designed to withstand overtemperature for extended periods.

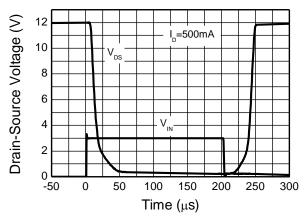


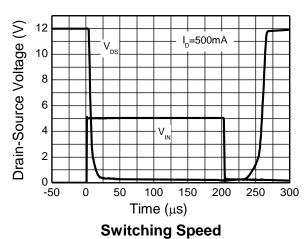
Typical Performance Characteristics





Typical Performance Characteristics (continued)





Switching Speed

Typical Short Circuit Protection

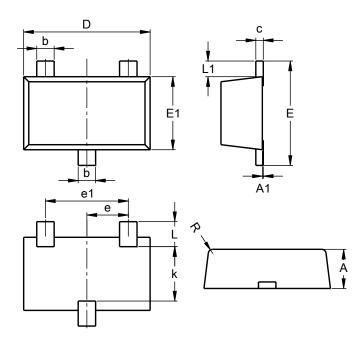
Time (ms)



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23F

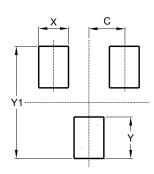


SOT23F					
Dim	Min	Max	Тур		
Α	0.80	1.00	0.90		
A1	0.00	0.10	0.01		
b	0.35	0.50	0.44		
С	0.10	0.20	0.16		
D	2.80	3.00	2.90		
е	0.95 REF				
e1	1.90 REF				
Е	2.30	2.50	2.40		
E1	1.50	1.70	1.65		
k	1.20	-	-		
L	0.30	0.65	0.50		
L1	0.30	0.50	0.40		
R	0.05	0.15	-		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23F



Dimensions	Value (in mm)		
C	0.95		
Х	0.80		
Υ	1.110		
Y1	3.000		



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